PESD1CAN

CAN bus ESD protection diode

Rev. 04 — 15 February 2008

1. Product profile

1.1 General description

PESD1CAN in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package designed to protect two automotive Controller Area Network (CAN) bus lines from the damage caused by ElectroStatic Discharge (ESD) and other transients.

1.2 Features

■ Due to the integrated diode structure only one small SOT23 package is needed to protect two CAN bus lines

■ Max. peak pulse power: P_{PP} = 200 W at t_p = 8/20 μs

■ Low clamping voltage: V_{CL} = 40 V at I_{PP} = 1 A

■ Ultra low leakage current: I_{RM} < 1 nA

■ Typ. diode capacitance matching: $\Delta C_d/C_d$ = 0.1 %

■ ESD protection up to 23 kV

■ IEC 61000-4-2, level 4 (ESD)

■ IEC 61000-4-5 (surge); I_{PP} = 3 A at t_p = 8/20 μs

■ Small SMD plastic package

1.3 Applications

■ CAN bus protection
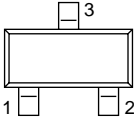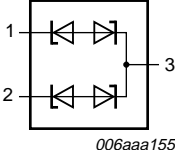
■ Automotive applications

1.4 Quick reference data

Table 1.   Quick reference data

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
V_{RWM}	reverse standoff voltage		-	-	24	V
C_d	diode capacitance	f = 1 MHz; V_R = 0 V	-	11	17	pF

NXP

founded by Philips

2. Pinning information

Table 2.   Pinning

Pin	Description	Simplified outline	Symbol
1	cathode 1		
2	cathode 2		
3	common cathode		

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3. Ordering information

Table 3.   Ordering information

Type number	Package		
	Name	**Description**	**Version**
PESD1CAN	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4.   Marking codes

Type number	Marking code[1]
PESD1CAN	*AN

[1]   * = -: made in Hong Kong

       * = p: made in Hong Kong

       * = t: made in Malaysia

       * = W: made in China

5. Limiting values

Table 5.   Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
P_{PP}	peak pulse power	$t_p = 8/20$ μs	[1][2]	-	200	W
I_{PP}	peak pulse current	$t_p = 8/20$ μs	[1][2]	-	3	A
Per device						
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			−65	+150	°C
T_{stg}	storage temperature			−65	+150	°C

[1]   Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC 61000-4-5.

[2]   Measured from pin 1 to 3 or 2 to 3.

Table 6.   ESD maximum ratings

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V_{ESD}	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	23	kV
		MIL-STD-883 (human body model)		-	10	kV

[1]   Device stressed with ten non-repetitive ESD pulses.

[2]   Measured from pin 1 to 3 or 2 to 3.

Table 7.   ESD standards compliance

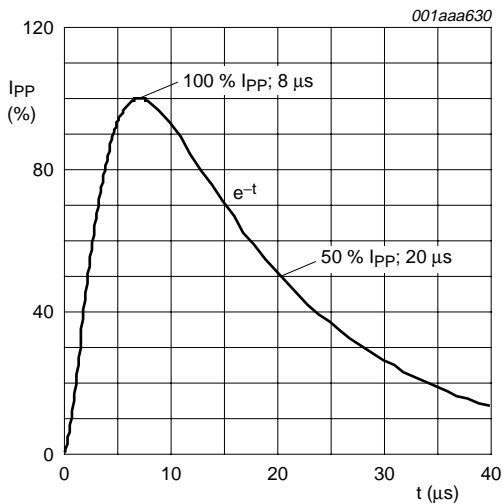| Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV

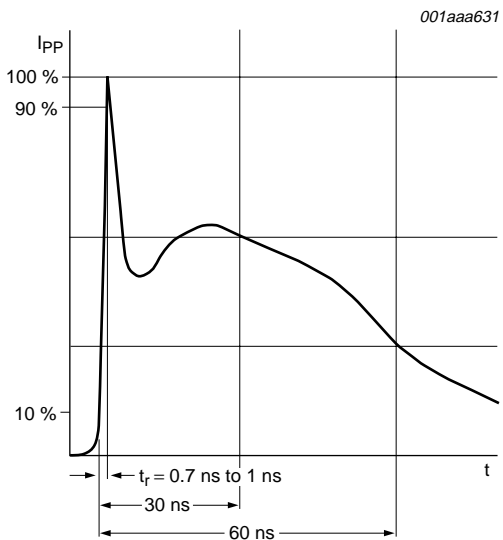**Fig 1.   8/20 μs pulse waveform according to IEC 61000-4-5**

Fig 2.   ESD pulse waveform according to IEC 61000-4-2

# 6. Characteristics

Table 8.   Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
V_{RWM}	reverse standoff voltage		-	-	24	V
I_{RM}	reverse leakage current	V_{RWM} = 24 V	-	< 1	50	nA
V_{BR}	breakdown voltage	I_R = 5 mA	25.4	27.8	30.3	V
C_d	diode capacitance	f = 1 MHz; V_R = 0 V	-	11	17	pF
$\Delta C_d/C_d$	diode capacitance matching	[1]				
		f = 1 MHz; V_R = 0 V	-	0.1	-	%
		f = 1 MHz; V_R = 2.5 V	-	0.1	-	%
V_{CL}	clamping voltage	[2][3]				
		I_{PP} = 1 A	-	-	40	V
		I_{PP} = 3 A	-	-	70	V
r_{dif}	differential resistance	I_R = 1 mA	-	-	300	Ω

[1] ΔC_d is the difference of the capacitance measured between pin 1 and pin 3 and the capacitance measured between pin 2 and pin 3.

[2]   Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC 61000-4-5.

[3]   Measured from pin 1 to 3 or 2 to 3.

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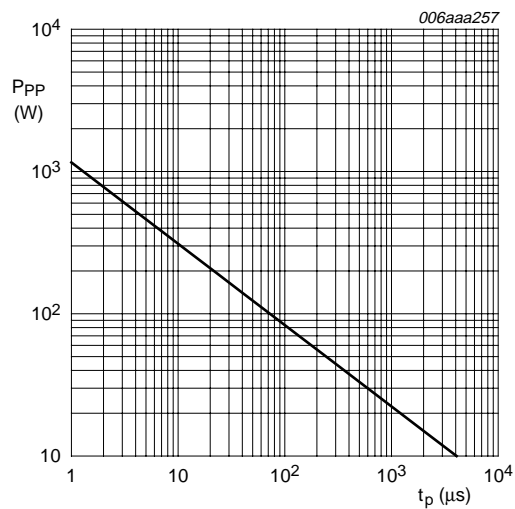
$T_{amb} = 25\ °C$

Fig 3. Peak pulse power as a function of exponential pulse duration; typical values
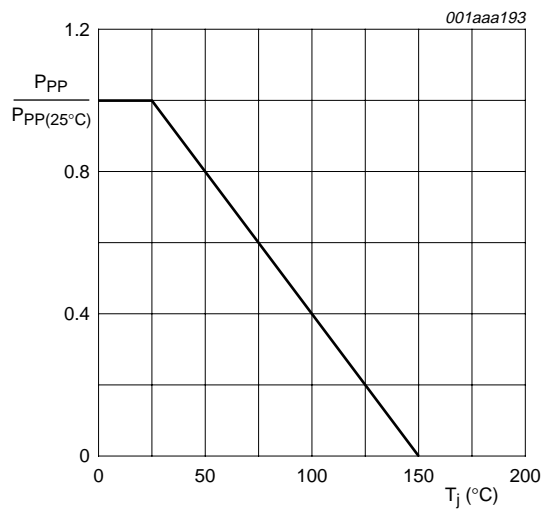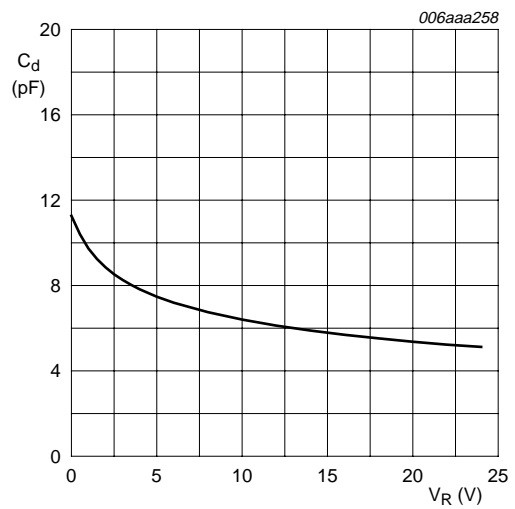

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Fig 4. Relative variation of peak pulse power as a function of junction temperature; typical values

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$f = 1\ MHz;\ T_{amb} = 25\ °C$

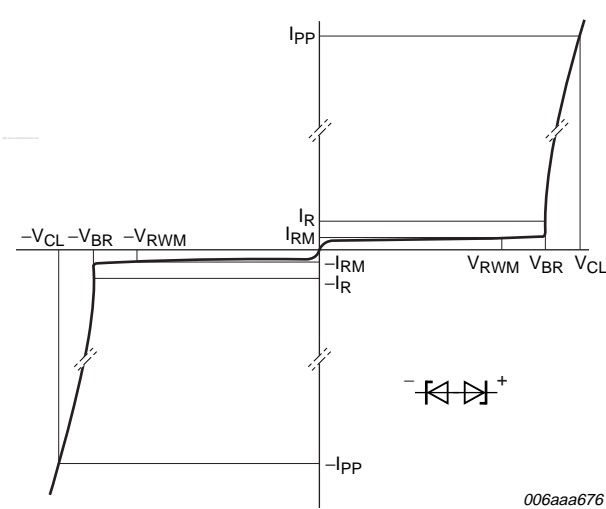**Fig 5.** Diode capacitance as a function of reverse voltage; typical values

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Fig 6. V-I characteristics for a bidirectional ESD protection diode

unclamped +1 kV ESD voltage waveform
(IEC 61000-4-2 network)

vertical scale = 200 V/div
horizontal scale = 50 ns/div

clamped +1 kV ESD voltage waveform
(IEC 61000-4-2 network)

vertical scale = 20 V/div;   horizontal scale = 50 ns/div

unclamped −1 kV ESD voltage waveform
(IEC 61000-4-2 network)

vertical scale = 200 V/div
horizontal scale = 50 ns/div

clamped −1 kV ESD voltage waveform
(IEC 61000-4-2 network)

vertical scale = 20 V/div;   horizontal scale = 50 ns/div

ESD TESTER

R_Z

C_Z

IEC 61000-4-2 network
C_Z = 150 pF; R_Z = 330 Ω

D.U.T.
(Device Under Test)

450 Ω

RG 223/U
50 Ω coax

10×
ATTENUATOR
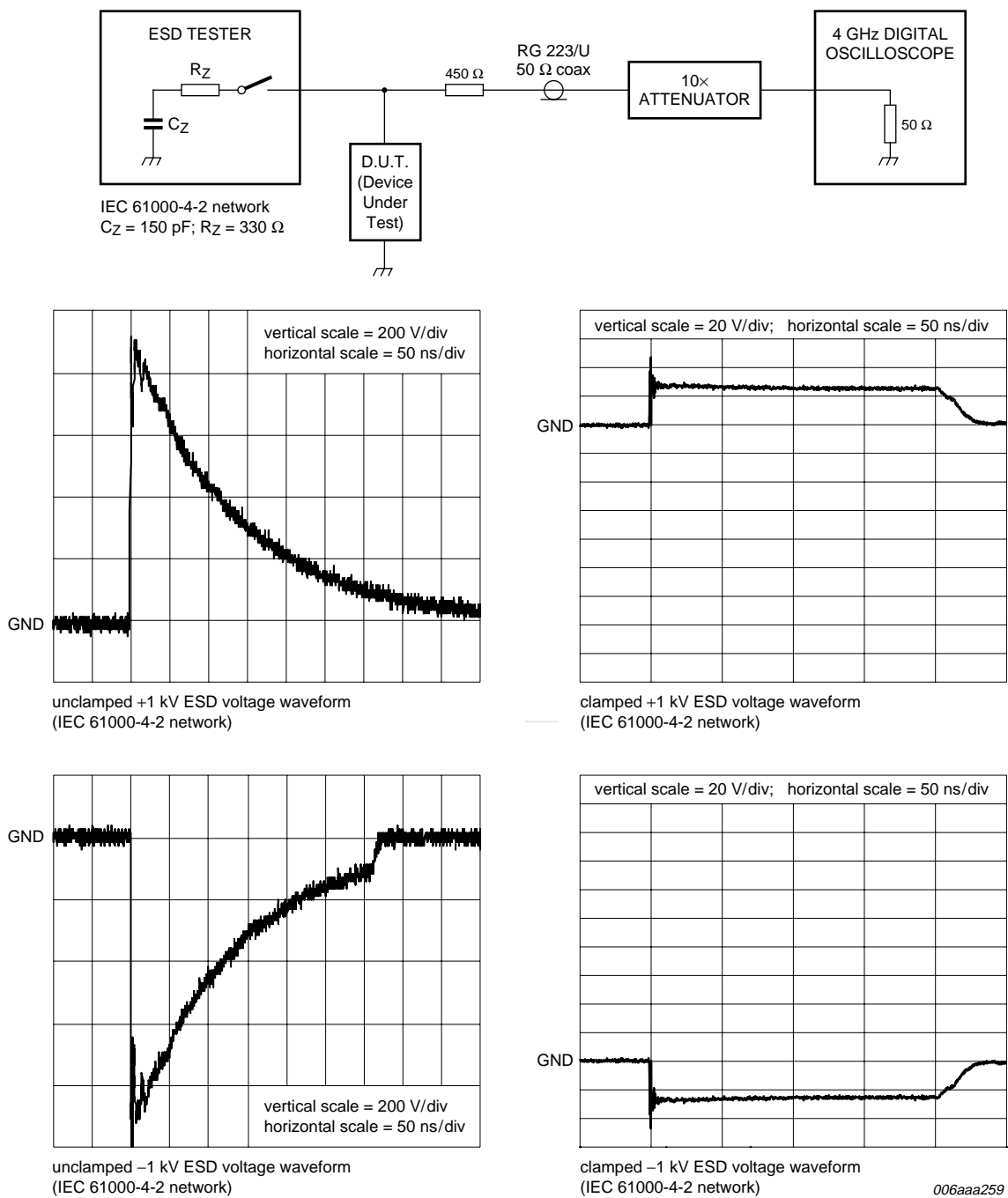
4 GHz DIGITAL OSCILLOSCOPE

50 Ω

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Fig 7.   ESD clamping test setup and waveforms

7. Application information

The PESD1CAN is designed for the protection of two automotive CAN bus lines from the damage caused by ESD and surge pulses. The device can be used for both, high-speed CAN bus and fault-tolerant CAN bus protection. The PESD1CAN provides a surge capability of up to 200 W per line for an 8/20 μs waveform.
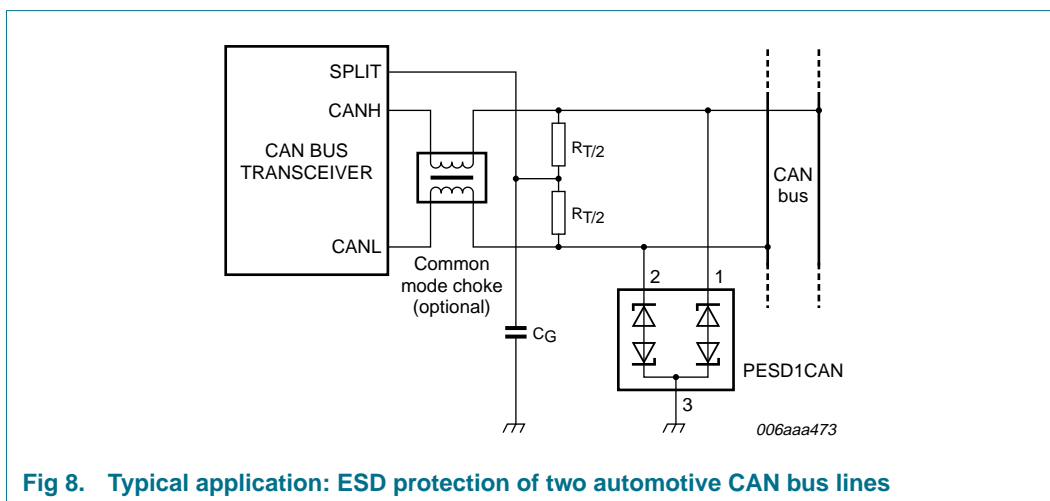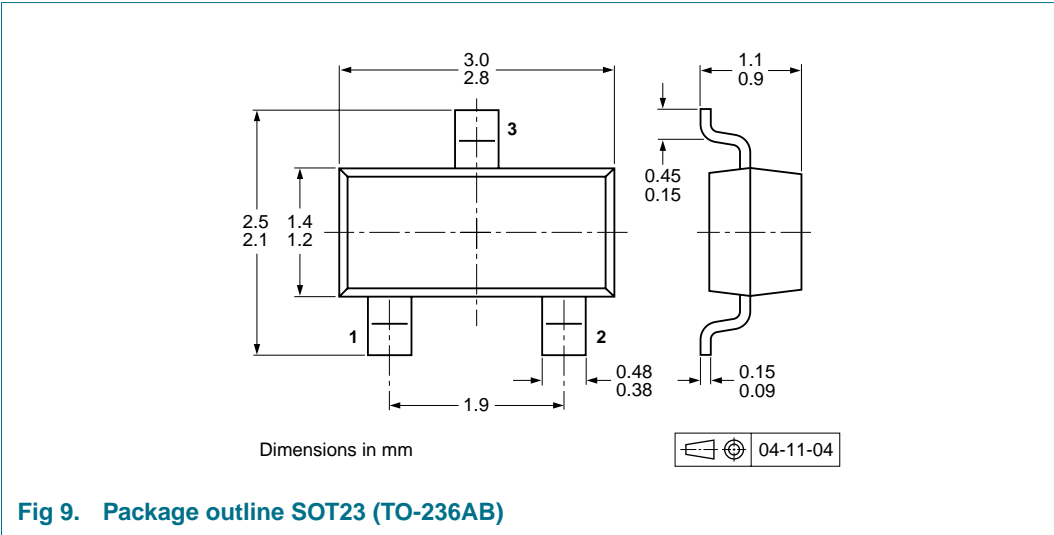

Fig 8.   Typical application: ESD protection of two automotive CAN bus lines

Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

1. Place the PESD1CAN as close to the input terminal or connector as possible.
2. The path length between the PESD1CAN and the protected line should be minimized.
3. Keep parallel signal paths to a minimum.
4. Avoid running protection conductors in parallel with unprotected conductors.
5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
6. Minimize the length of the transient return path to ground.
7. Avoid using shared transient return paths to a common ground point.
8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

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8. Package outline

Dimensions in mm

Fig 9.   Package outline SOT23 (TO-236AB)

9. Packing information

Table 9.   Packing methods
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	**10000**
PESD1CAN	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1]   For further information and the availability of packing methods, see Section 13.
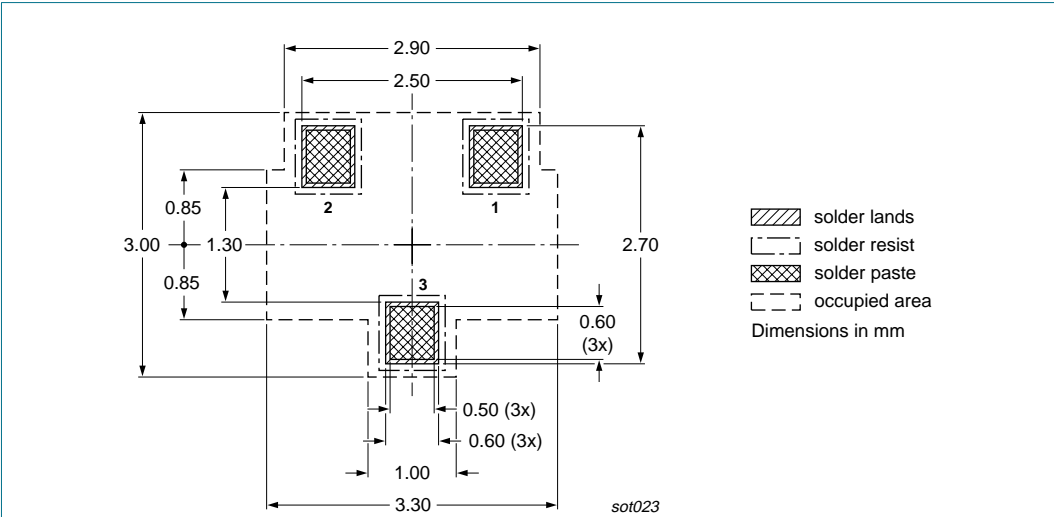
10. Soldering
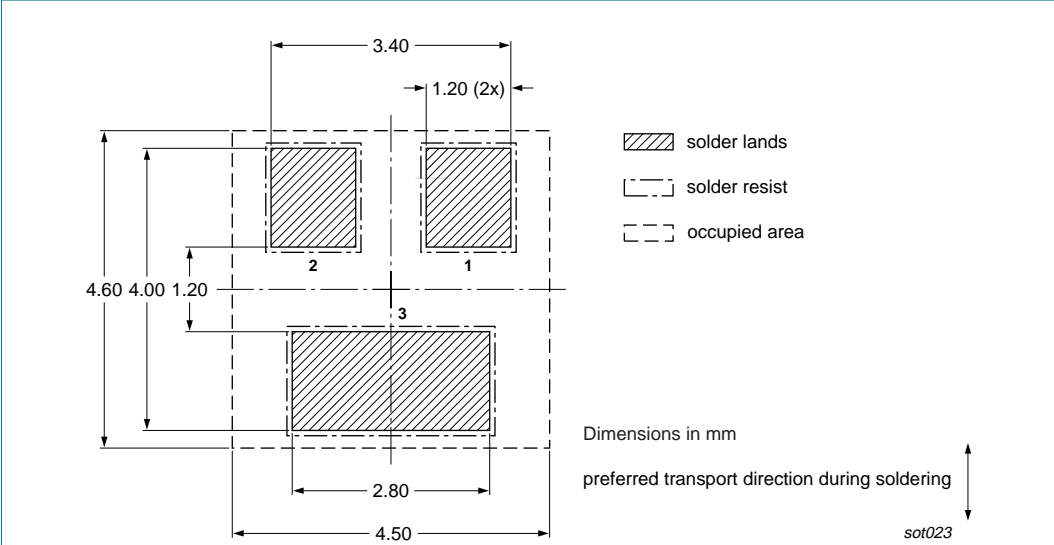

Fig 10. Reflow soldering footprint SOT23 (TO-236AB)

Fig 11. Wave soldering footprint SOT23 (TO-236AB)

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD1CAN_4	20080215	Product data sheet	-	PESD1CAN_3
Modifications:		• Section 1.2 "Features": list item for diode capacitance matching added • Table 8 "Characteristics": $\Delta C_d/C_d$ diode capacitance matching added		
PESD1CAN_3	20070521	Product data sheet	-	PESD1CAN_2
PESD1CAN_2	20051017	Product data sheet	-	PESD1CAN_1
PESD1CAN_1	20050125	Objective data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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